



AMPLIFIER TRANSISTOR

Collector-Emitter Voltage: $V_{ce}=160V$.

Collector Dissipation: $P_c(\max)=625mW$

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$)

T_{stg} — Storage Temperature..... $-55\sim 150^{\circ}C$

T_j — Junction Temperature..... $150^{\circ}C$

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P_C — Collector Dissipation..... $625mW$

V_{CBO} — Collector-Base Voltage..... $180V$

V_{CEO} — Collector-Emitter Voltage..... $160V$

V_{EBO} — Emitter-Base Voltage..... $6V$

I_C — Collector Current..... $600mA$

TO-92



1—Emitter, E

2—Base, B

3—Collector, C

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	180			V	$I_C=100\mu A$, $I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	160			V	$I_C=1mA$, $I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	6			V	$I_E=10\mu A$, $I_C=0$
I_{CBO}	Collector Cut-off Current			50	nA	$V_{CB}=120V$, $I_E=0$
I_{EBO}	Emitter-Base Cut-off Current			50	nA	$V_{EB}=4V$, $I_C=0$
H_{FE} (1)	DC Current Gain	80				$V_{CE}=5V$, $I_C=1mA$
H_{FE} (2)		80		280		$V_{CE}=5V$, $I_C=10mA$
H_{FE} (3)		30				$V_{CE}=5V$, $I_C=50mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			0.15	V	$I_C=10mA$, $I_B=-1mA$
$V_{CE(sat2)}$				0.2	V	$I_C=50mA$, $I_B=5mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			1	V	$I_C=10mA$, $I_B=1mA$
$V_{BE(sat2)}$				1	V	$I_C=50mA$, $I_B=5mA$,
f_T	Current Gain-Bandwidth Product	100		300	MHz	$V_{CE}=10V$, $I_C=10mA$ $F=100MHz$